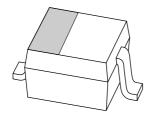
### DISCRETE SEMICONDUCTORS

# DATA SHEET



# BAP63-03 Silicon PIN diode

Product specification Supersedes data of 2001 May 18 2004 Feb 11





Silicon PIN diode BAP63-03

#### **FEATURES**

- High speed switching for RF signals
- Low diode capacitance
- Low diode forward resistance
- Very low series inductance
- For applications up to 3 GHz.

#### **APPLICATIONS**

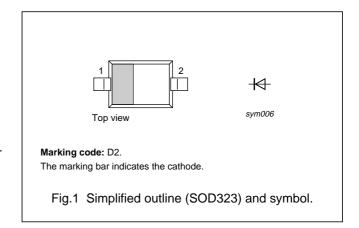
• RF attenuators and switches.

#### **DESCRIPTION**

Planar PIN diode in a SOD323 small SMD plastic package.

#### **PINNING**

PIN	DESCRIPTION
1	cathode
2	anode



#### **ORDERING INFORMATION**

TYPE	PACKAGE				
NUMBER	NAME	NAME DESCRIPTION			
BAP63-03	_	plastic surface mounted package; 2 leads	SOD323		

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		_	50	V
I <sub>F</sub>	continuous forward current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> ≤ 90 °C	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-65	+150	°C

Silicon PIN diode BAP63-03

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 mA	0.95	1.1	V
I <sub>R</sub>	reverse leakage current	V <sub>R</sub> = 35 V	_	10	nA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0; f = 1 MHz	0.4	_	pF
		V <sub>R</sub> = 1 V; f = 1 MHz	0.35	_	pF
		V <sub>R</sub> = 20 V; f = 1 MHz	0.27	0.32	pF
r <sub>D</sub>	diode forward resistance	I <sub>F</sub> = 0.5 mA; f = 100 MHz; note 1	2.5	3.5	Ω
		I <sub>F</sub> = 1 mA; f = 100 MHz; note 1	1.95	3	Ω
		I <sub>F</sub> = 10 mA; f = 100 MHz; note 1	1.17	1.8	Ω
		I <sub>F</sub> = 100 mA; f = 100 MHz; note 1	0.9	1.5	Ω
S <sub>21</sub>   <sup>2</sup>	isolation	V <sub>R</sub> = 0; f = 900 MHz	15.4	_	dB
		V <sub>R</sub> = 0; f = 1800 MHz	10.1	_	dB
		V <sub>R</sub> = 0; f = 2450 MHz	7.8	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 0.5 mA; f = 900 MHz	0.21	_	dB
		I <sub>F</sub> = 0.5 mA; f = 1800 MHz	0.28	_	dB
		I <sub>F</sub> = 0.5 mA; f = 2450 MHz	0.38	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 1 mA; f = 900 MHz	0.18	_	dB
		I <sub>F</sub> = 1 mA; f = 1800 MHz	0.26	_	dB
		I <sub>F</sub> = 1 mA; f = 2450 MHz	0.35	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 10 mA; f = 900 MHz	0.13	_	dB
		I <sub>F</sub> = 10 mA; f = 1800 MHz	0.20	_	dB
		I <sub>F</sub> = 10 mA; f = 2450 MHz	0.30	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 100 mA; f = 900 MHz	0.10	_	dB
		I <sub>F</sub> = 100 mA; f = 1800 MHz	0.18	_	dB
		I <sub>F</sub> = 100 mA; f = 2450 MHz	0.28	_	dB
τ∟	charge carrier life time	when switched from $I_F$ = 10 mA to $I_R$ = 6 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 3 mA	310	-	ns
L <sub>S</sub>	series inductance		1.5	_	nH

#### Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th(j-s)}$	thermal resistance from junction to soldering point	120	K/W

#### Silicon PIN diode BAP63-03

#### **GRAPHICAL DATA**

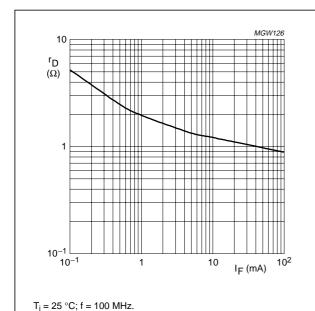


Fig.2 Forward resistance as a function of forward current; typical values.

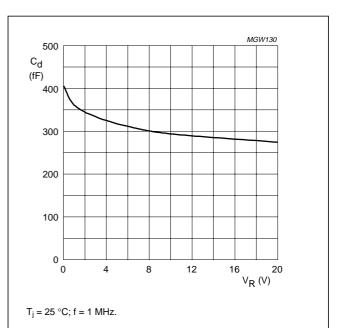


Fig.3 Diode capacitance as a function of reverse voltage; typical values.

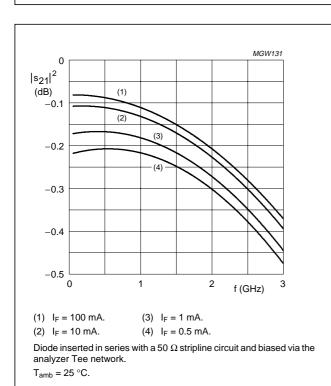
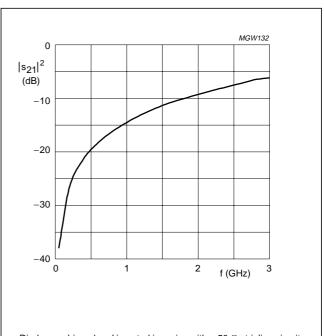


Fig.4 Insertion loss ( $|s_{21}|^2$ ) of the diode in on-state as a function of frequency; typical values.



Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit.  $\rm T_{amb}$  = 25  $^{\circ}C.$ 

Fig.5 Isolation (|s<sub>21</sub>|<sup>2</sup>) of the diode in off-state as a function of frequency; typical values.

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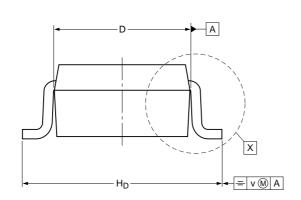
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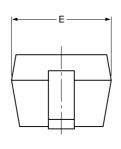
Silicon PIN diode BAP63-03

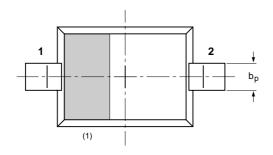
#### **PACKAGE OUTLINE**

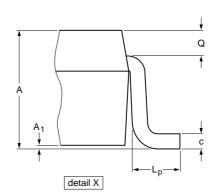
#### Plastic surface mounted package; 2 leads

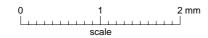
SOD323











#### DIMENSIONS (mm are the original dimensions)

UNIT	Α	A <sub>1</sub> max	bp	С	D	E	H <sub>D</sub>	Lp	Q	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15		0.2

#### Note

1. The marking bar indicates the cathode

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOD323			SC-76			<del>99-09-13</del> 03-12-17

Silicon PIN diode BAP63-03

#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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